

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Ricky Amos

Group Art Unit: 2815  
*#87/Amos/B  
Chas  
Landau  
3/27/03*

Serial No.: 09/995,031

Examiner: Matthew Landau

Filed: Nov. 29, 2001

In Response to Office Action  
Dated: Jan. 22, 2003For: High Temperature Processing Compatible Metal Gate  
Electrode For FETs and Method for Fabrication

Attorney Docket No.: YOR920010633US1 (062)

*Ricky Amos*  
Certificate of Facsimile  
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TECHNOLOGY CENTER 2800

REQUEST FOR RECONSIDERATIONAssistant Commissioner  
for Patents  
Washington, D.C. 20231

Dear Sir:

In response to a final Office Action mailed January 22, 2003, please enter the following amendments and consider the following remarks.